

# Silicon Variable Capacitance Diode

- For FM radio tuner with extended frequency band
- High tuning ratio at low supply voltage (car radio)
- Monolitic chip (common cathode) for perfect dual diode tracking
- Good linearity for C- V curve
- High figure of merit
- Pb-free (RoHS compliant) package<sup>1)</sup>
- Qualified according AEC Q101



### BB914

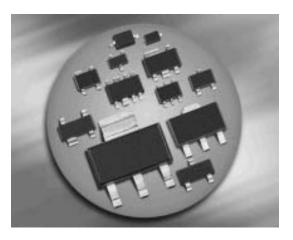


Туре	Package	Configuration	<b>L<sub>S</sub></b> (nH)	Marking
BB914	SOT23	common cathode	1.8	SM

## **Maximum Ratings** at $T_A = 25^{\circ}$ C, unless otherwise specified

Parameter	Symbol	Value	Unit
Diode reverse voltage	V <sub>R</sub>	18	V
Peak reverse voltage	V <sub>RM</sub>	20	
( $R \ge 5 \mathrm{k}\Omega$ )			
Forward current	I <sub>F</sub>	50	mA
Operating temperature range		-55 125	°C
Storage temperature	T <sub>stg</sub>	-55 150	

<sup>1</sup>Pb-containing package may be available upon special request





Parameter	Symbol		Values		
		min.	typ.	max.	1
DC Characteristics	·			-	
Reverse current	I <sub>R</sub>	-	-		nA
<i>V</i> <sub>R</sub> = 16 V		-	-	20	
$V_{\rm R}$ = 16 V, $T_{\rm A}$ = 85 °C				200	
AC Characteristics					
Diode capacitance	CT				pF
$V_{\rm R}$ = 2 V, f = 1 MHz		42.5	43.75	45	
$V_{R} = 8 V, f = 1 MHz$		17.6	18.7	19.75	
Capacitance ratio	C <sub>T2</sub> /C <sub>T8</sub>	2.28	2.34	2.42	
$V_{\rm R} = 2 \text{ V}, V_{\rm R} = 8 \text{ V}, f = 1 \text{ MHz}$					
Capacitance matching <sup>1)</sup>	$\Delta C_{T}/C_{T}$	-	-	1.5	%
$V_{\rm R} = 2 \text{ V}, V_{\rm R} = 8 \text{ V}, f = 1 \text{ MHz}$					
Series resistance	r <sub>S</sub>	-	0.28	-	Ω
<i>V</i> <sub>R</sub> = 2 V, <i>f</i> = 100 MHz					

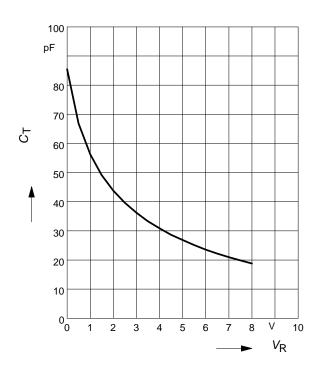
<b>Electrical Characteristics</b> at $T_A =$	= 25°C, unless otherwise specified
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<sup>1</sup>For details please refer to Application Note 047.

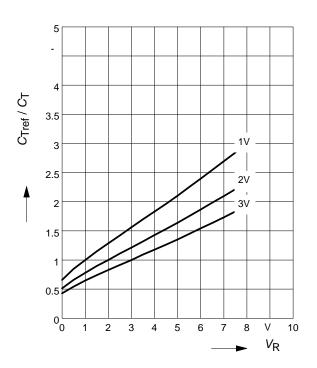


**Diode capacitance**  $C_{T} = f(V_{R})$ 

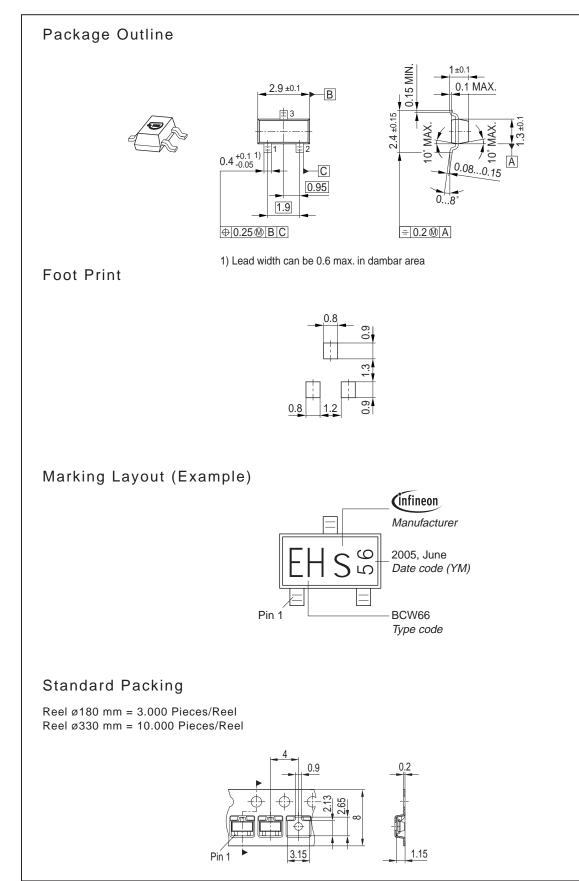
f = 1 MHz



**Capacitance ratio**  $C_{\text{Tref}}/C_{\text{T}} = f(V_{\text{R}})$ f = 1MHz









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